

Activities with the quadrupole resonator at HZB

O. Kugeler, S. Keckert, R. Kleindienst, J. Knobloch

Done most of the work

Master thesis
Start of PhD thesis

PhD thesis

EuCARD-2

3rd Annual WP12 Meeting at STFC Daresbury Laboratory

April 4th and 5th 2016

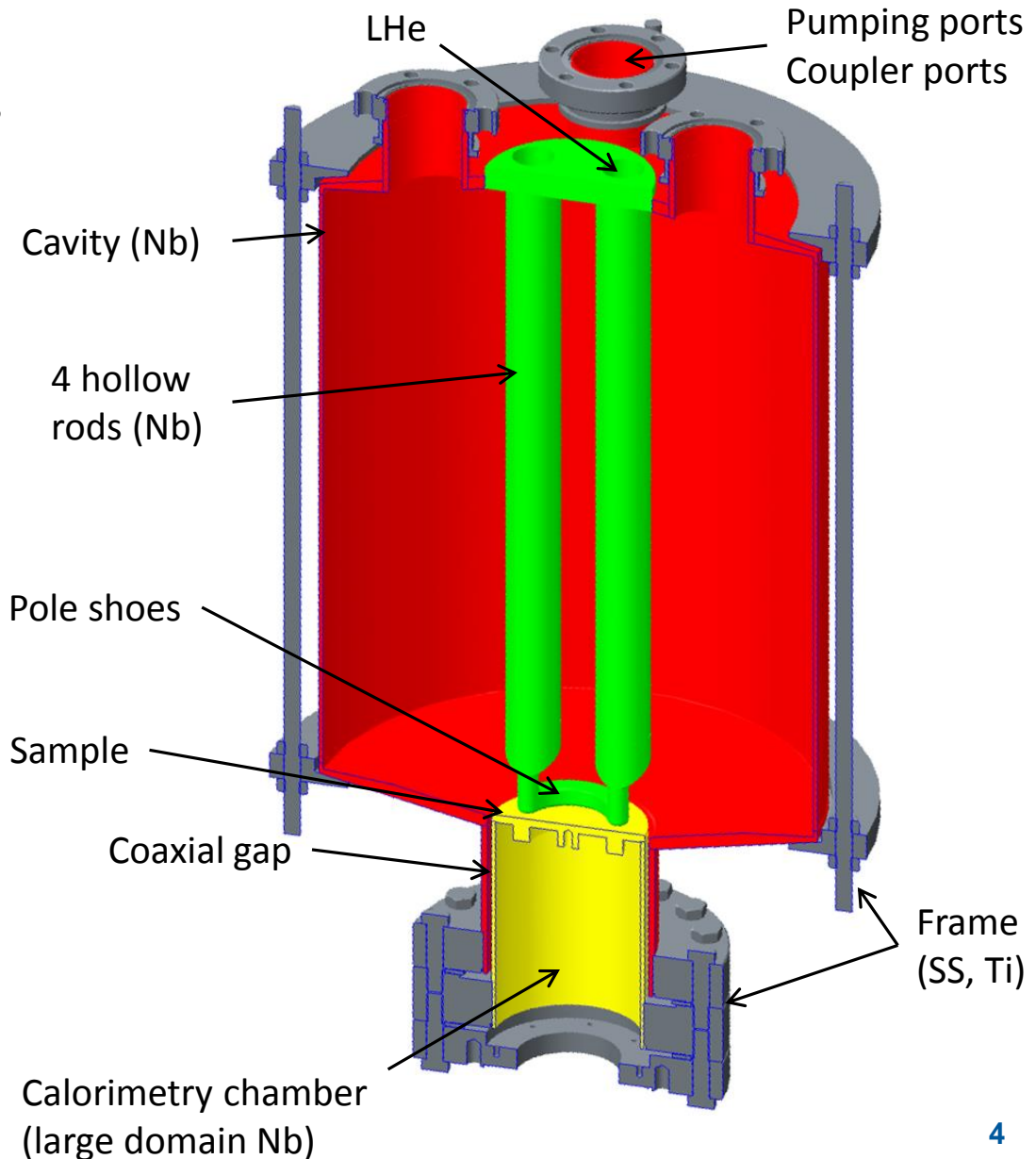
- Motivation
- QPR measurement principle
- Commissioning results
- Alternative sample chambers
- Example measurements
- Outlook

Characterization of superconducting samples

- Study „new“ superconductors
 - Thin films
 - Multilayer films
 - (enhanced Nb)
- What does an ideal tool look like?
(without going through the hassle of building an entire cavity)
 - Small and flat samples, easy to change
 - Measure RF surface resistance
 - Wide parameter space quickly available
 - ω, B_{RF}, T
 - High resolution: $Q_0 \approx 3 \cdot 10^{11} \leftrightarrow R_S \approx 1 \text{ n}\Omega$
 - Further sc properties
 - RF penetration depth, B_C , RRR, m.f.p., thermal conductivity
- Milestone 78 delivered in 10/2015

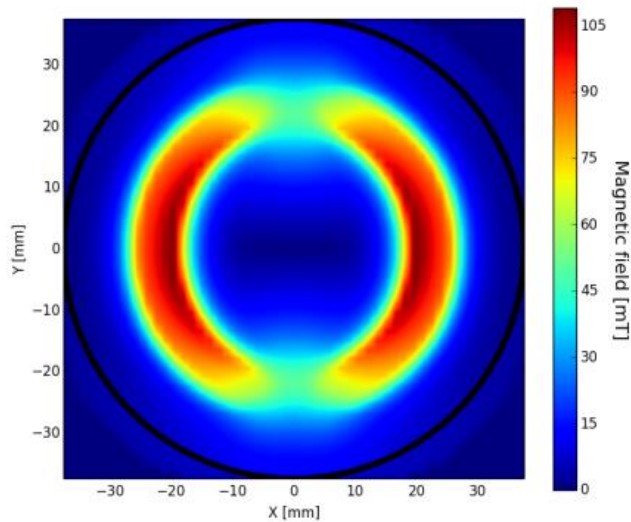
The Quadrupole Resonator (QPR)

- System based on CERN design
EPAC '98, Rev. Sci. Instrum. 74, 3390-3393
(2003)
- Optimized RF parameters
- Cavity and 4 hollow rods
made of Nb RRR 300
- 433 MHz or harmonics excited
with loop antenna

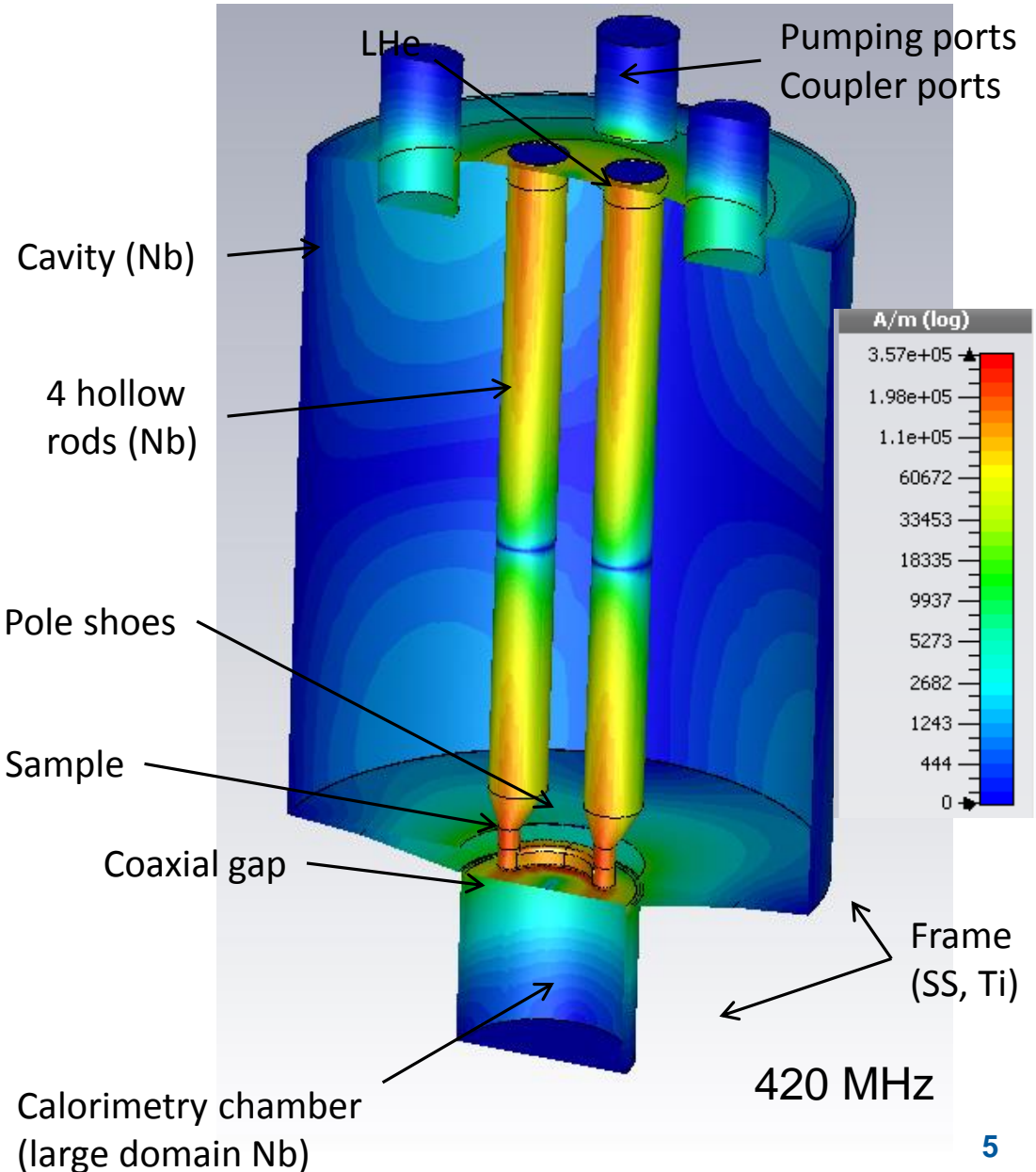


The Quadrupole Resonator (QPR)

- Pole shoes focus magnetic field on sample

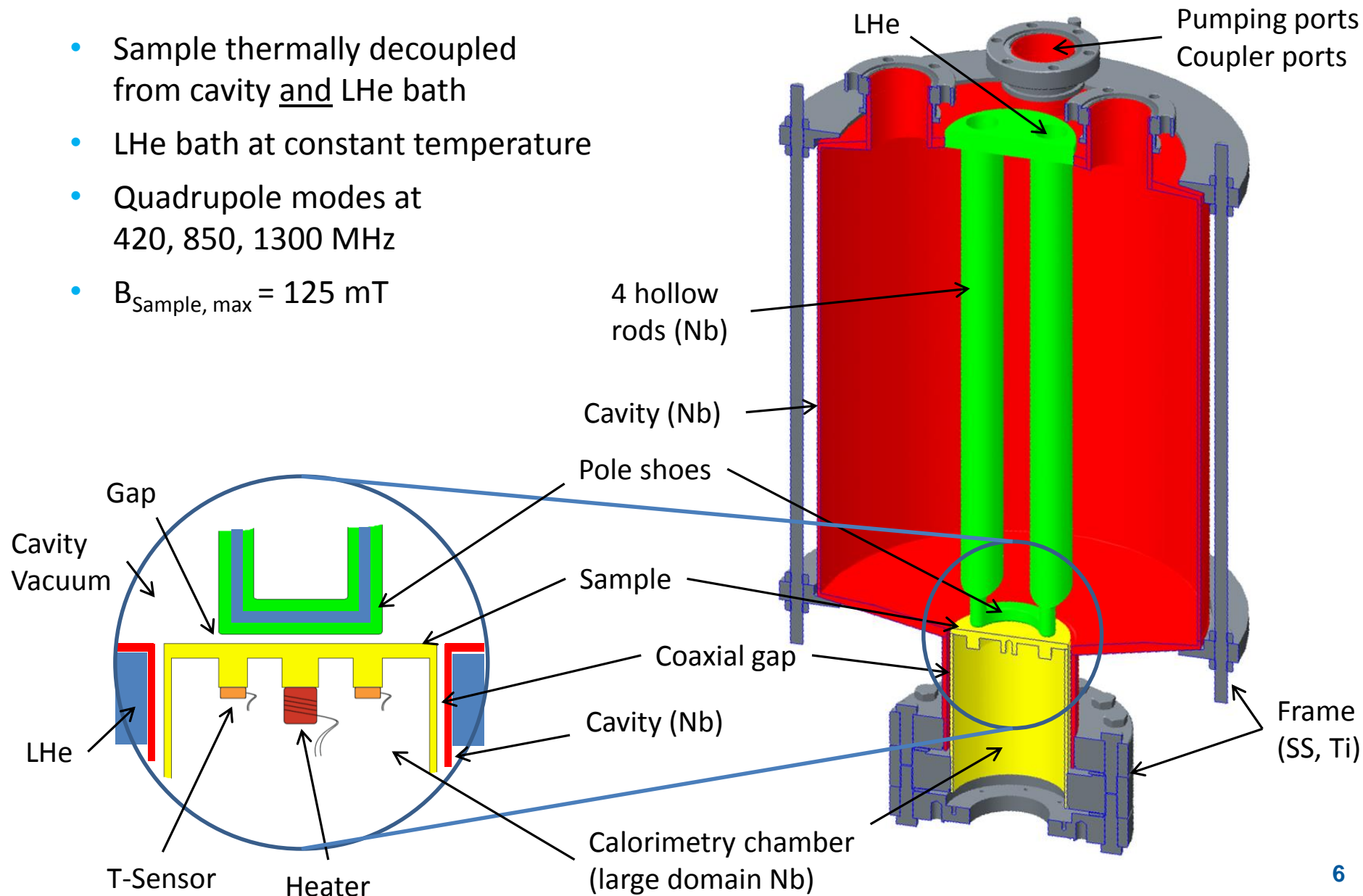


- Ring shaped region of sample illuminated
- Obtain geometry factor from simulation



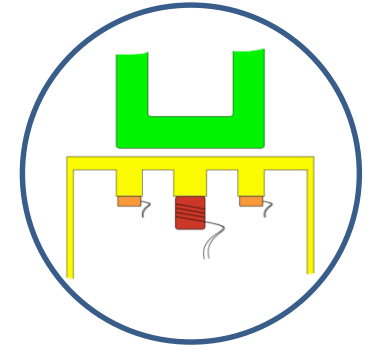
The Quadrupole Resonator (QPR)

- Sample thermally decoupled from cavity and LHe bath
- LHe bath at constant temperature
- Quadrupole modes at 420, 850, 1300 MHz
- $B_{\text{Sample, max}} = 125 \text{ mT}$



RF-DC compensation technique

- High precision: calorimetric measurement
 - Resolution: sub-nΩ
- Wide temperature range: 1.8 K up to $T > T_{c, Nb}$



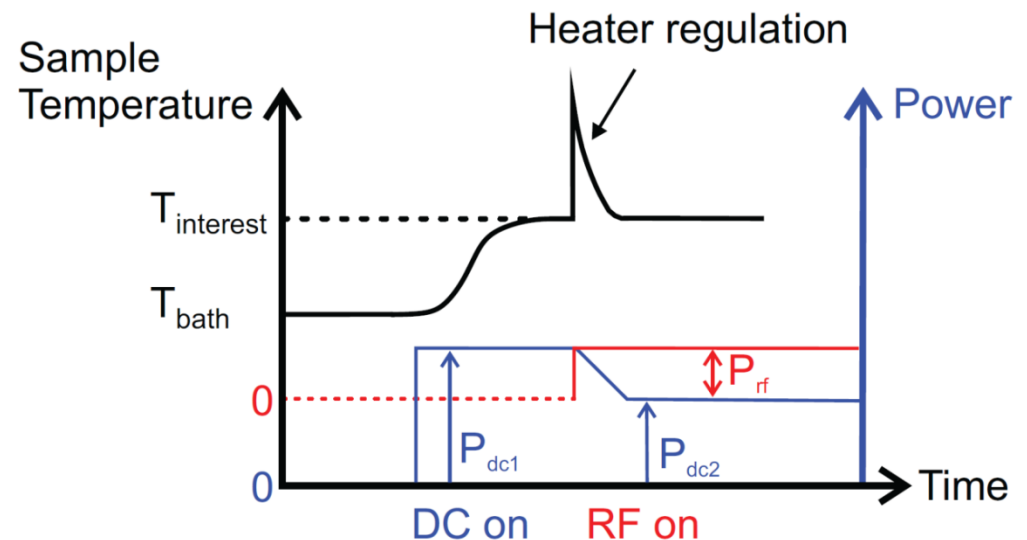
$$P_{RF} = \frac{1}{2} \iint_{sample} R_S |\vec{H}|^2 dS$$

$$P_{RF} = R_S \frac{\omega U}{G}$$

$$= P_{DC,1} - P_{DC,2}$$

$$\Rightarrow R_S = \frac{G}{\omega U} (P_{DC,1} - P_{DC,2})$$

$$\Rightarrow R_S = c(\omega) \cdot \frac{P_{DC,1} - P_{DC,2}}{P_{RF \text{ pickup}}}$$



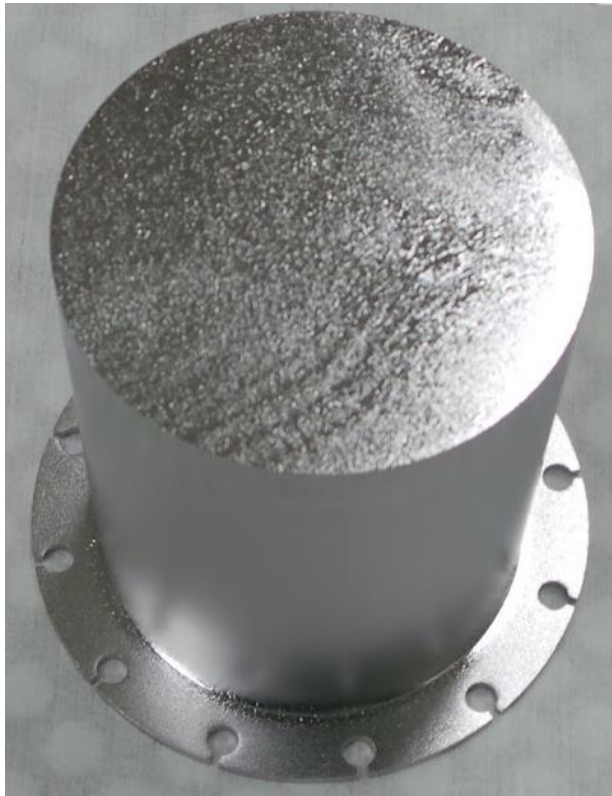
[S. Aull, „High Resolution Surface Resistance Studies“, SRF 2013]



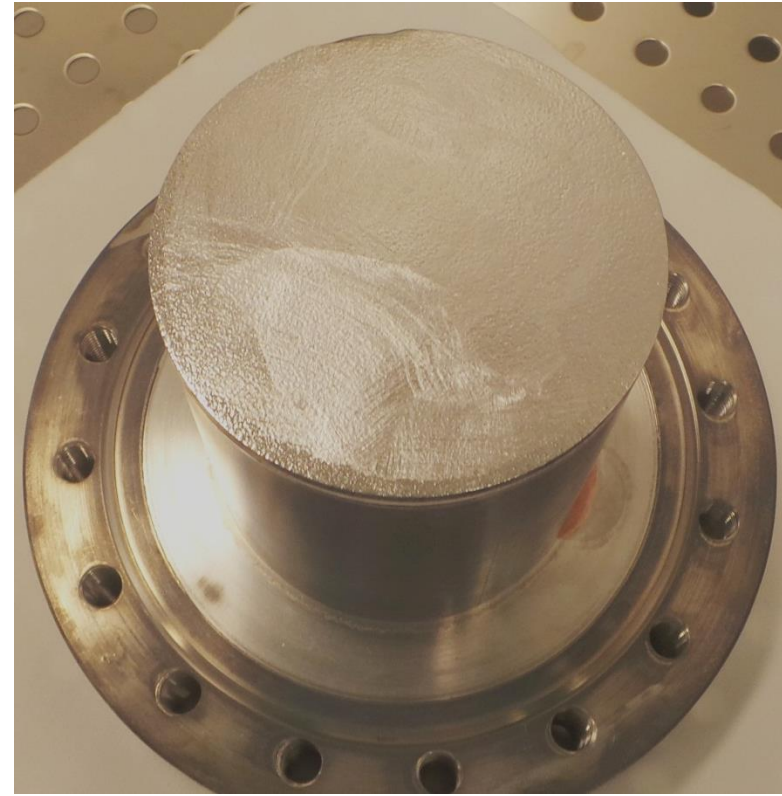
Clean room
assembly

Mounting in
the vertical
test stand in
the HoBiCaT
bunker

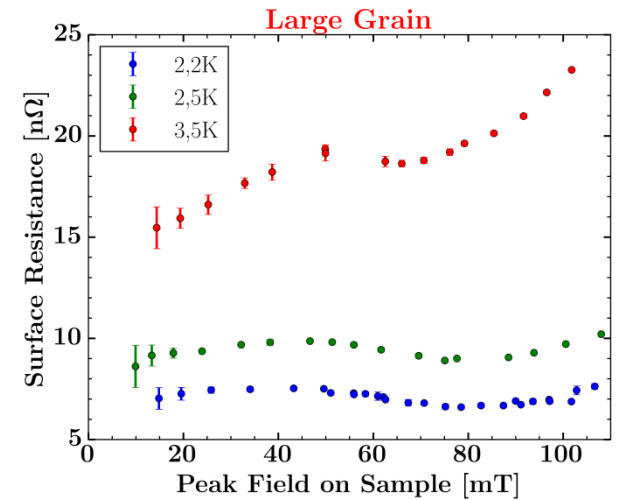
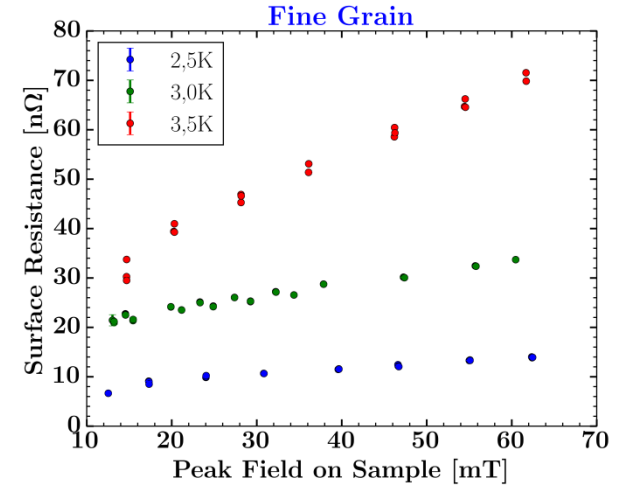
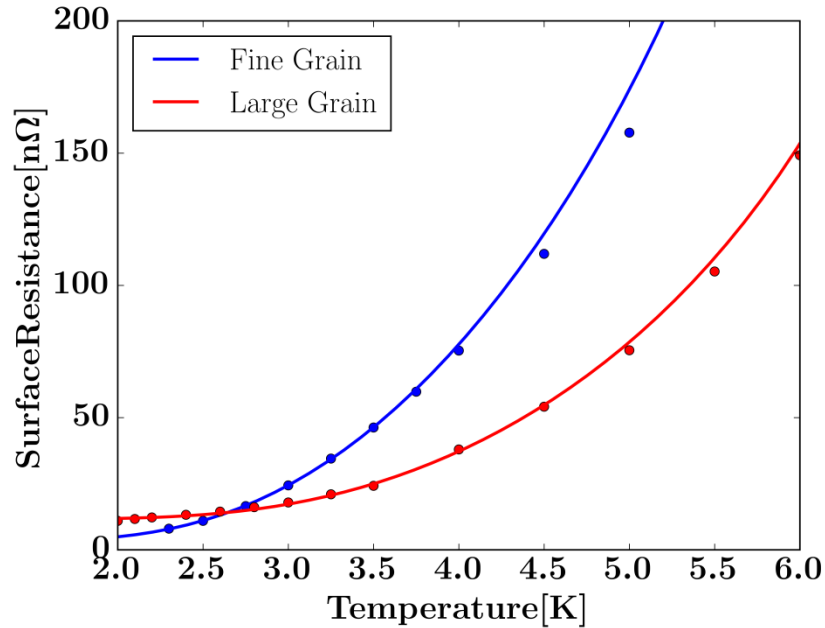




**Nb: Polychristalline RRR 300
BCP
+ High Temperature bake**

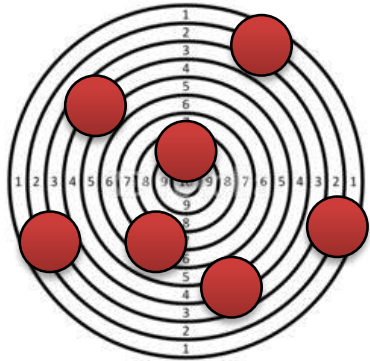


**Nb: Large Grain RRR 300
BCP
+ High Temperature bake
+ 120°C bake**

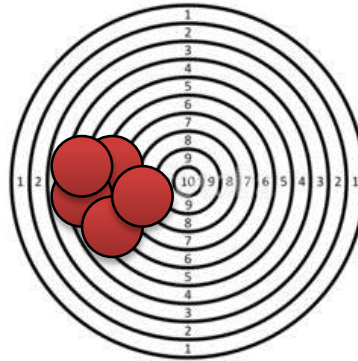


	Fine Grain BCP + HT	Large Grain BCP + HT +120°C
Energy gap	1.8 $k_B T_C$	2.1 $k_B T_C$
Electron m.f.p	68 nm	15 nm
Residual Res.	3.1 nΩ	7.6 nΩ

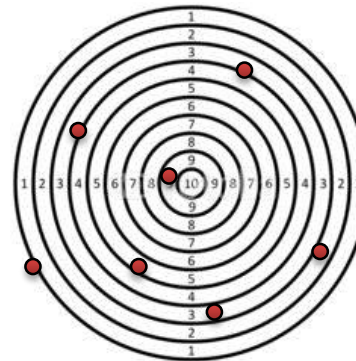
low precision
low accuracy
low resolution



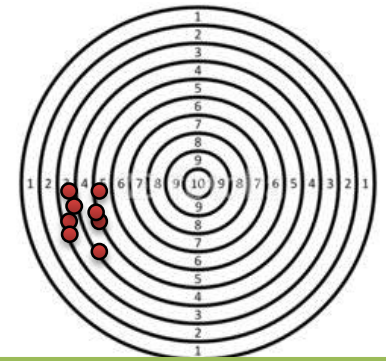
high precision
low accuracy
low resolution



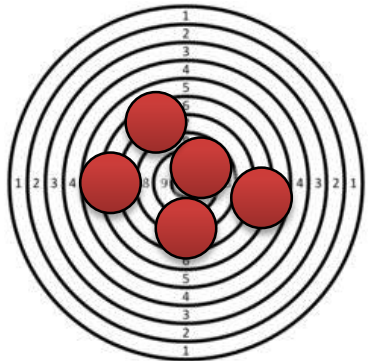
low precision
low accuracy
high resolution



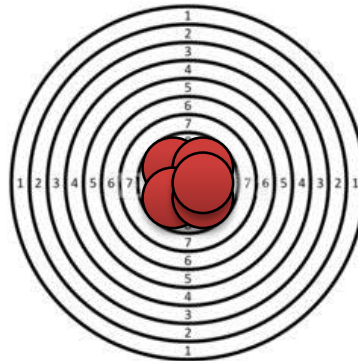
high precision
low accuracy
high resolution



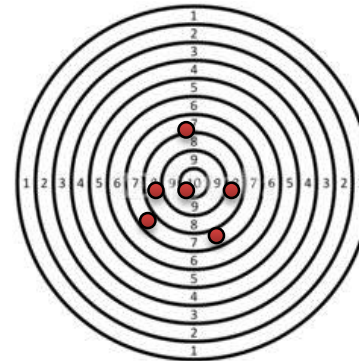
low precision
high accuracy
low resolution



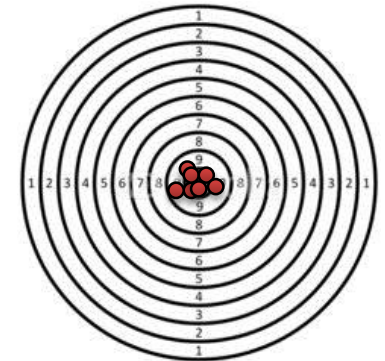
high precision
high accuracy
low resolution



low precision
high accuracy
high resolution



high precision
high accuracy
high resolution



- Systematic errors still unresolved
- Parallelity of gap critical
- Concentricity of rods and sample important

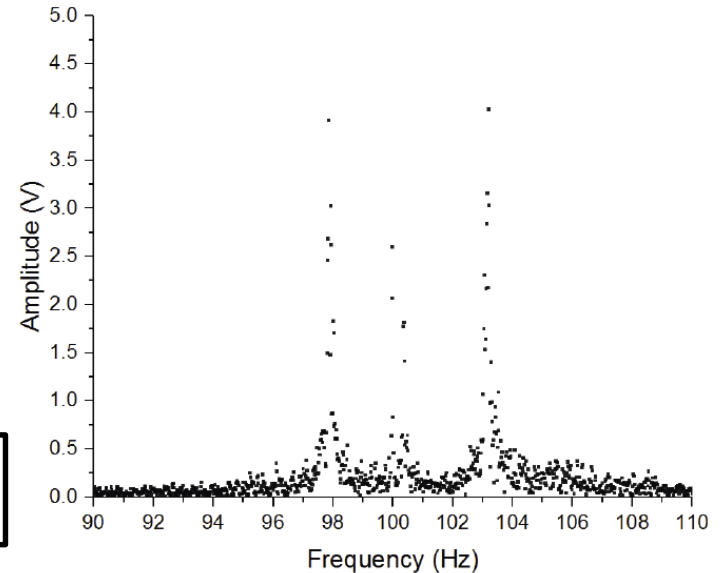
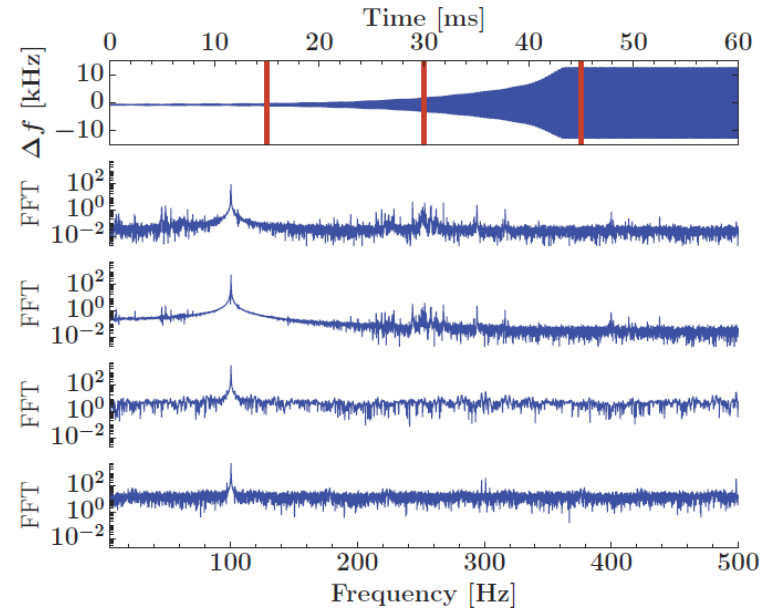
Microphonics is an issue

- Ponderomotive excitations observed
- Oscillation of the rods has resonance at 100 Hz (double mains frequency)
- Mode is always excited and needs to be compensated by PLL
- Complications, esp in pulsed OP

Countermeasures

- done: increased bandwidth of input antenna
- better: passive damping or piezo tuning

PLL feedback signal



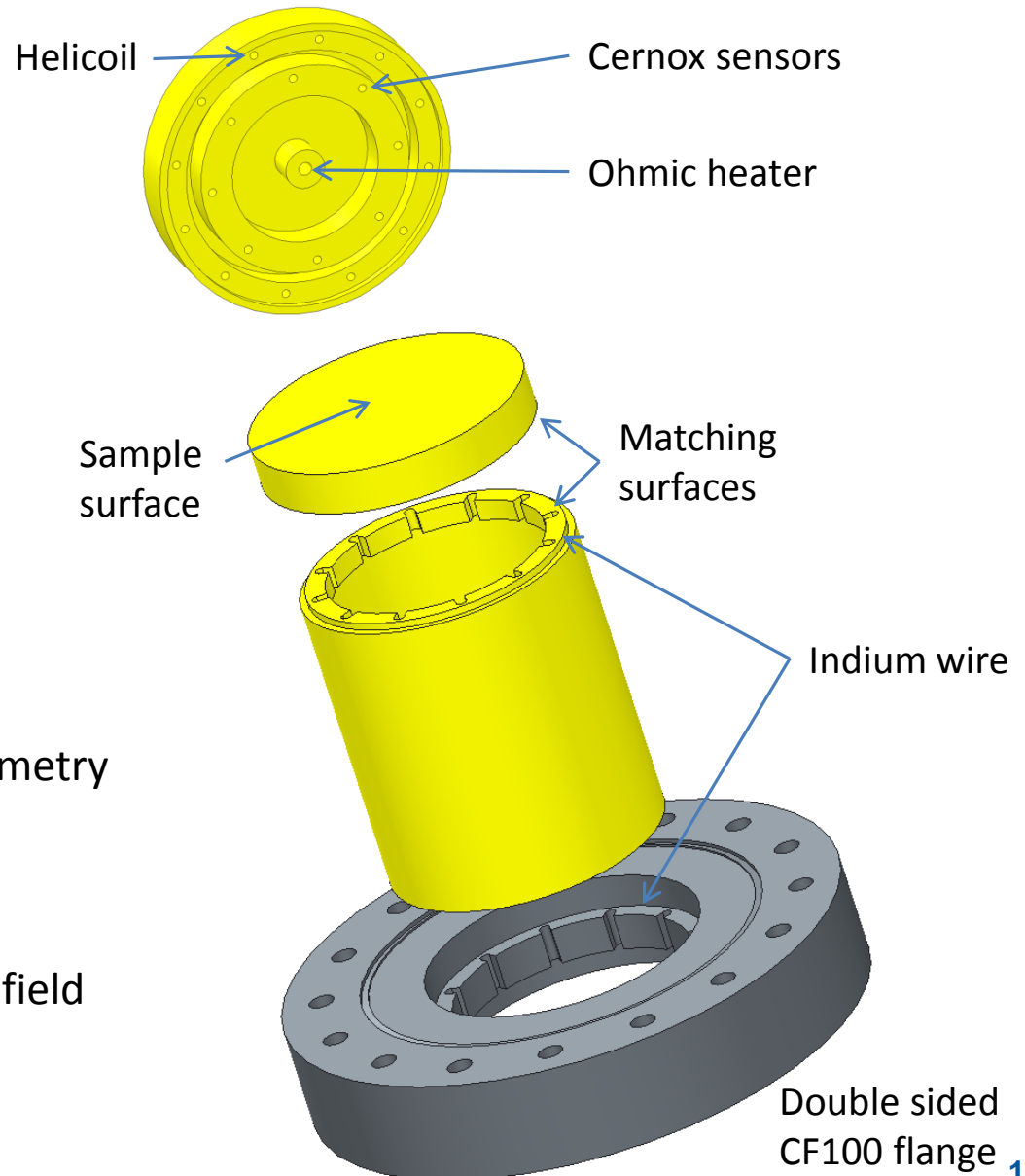
measured with geophones
at warm resonator

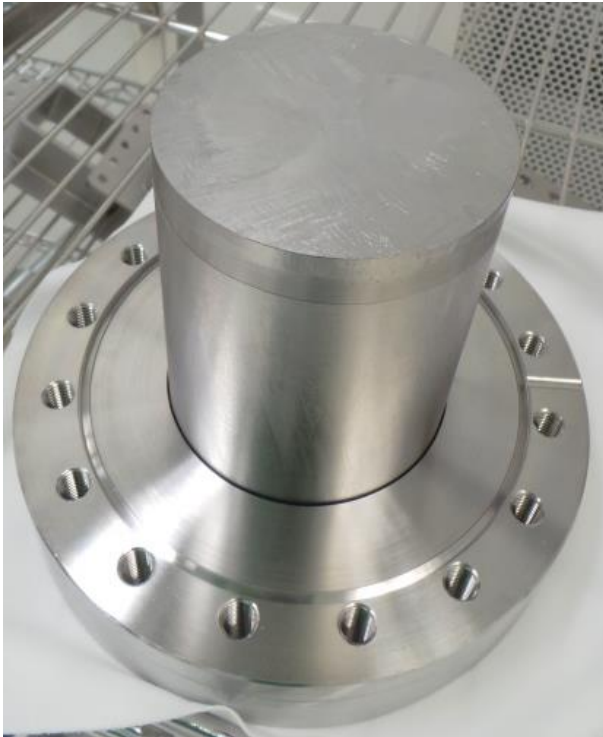
Motivation

- Short sample holder for coating
 $h = 12 \text{ mm}$
- Easier to handle
- No welding required
- Height adjustment possible
→ sensitivity on distance
between rods and sample

Risks

- Volumes of resonator and calorimetry chamber are connected
 - Cleanliness
 - Indium wire gaskets create additional risk: low quench field
- Thermal contact ?
- Impact on RF ?



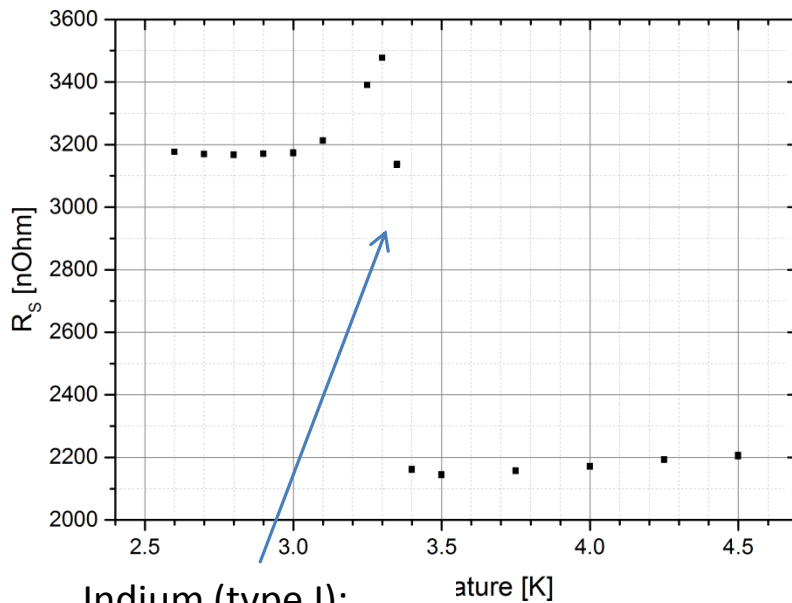


- milled from large-grain bulk
- Nb RRR 300
- 150 μm chemical etch (BCP)
- Surface roughness
 - max: 10 μm peak-to-peak
 - typ: 2 μm



- baked at 850°C / 240 min
- 150 μm BCP

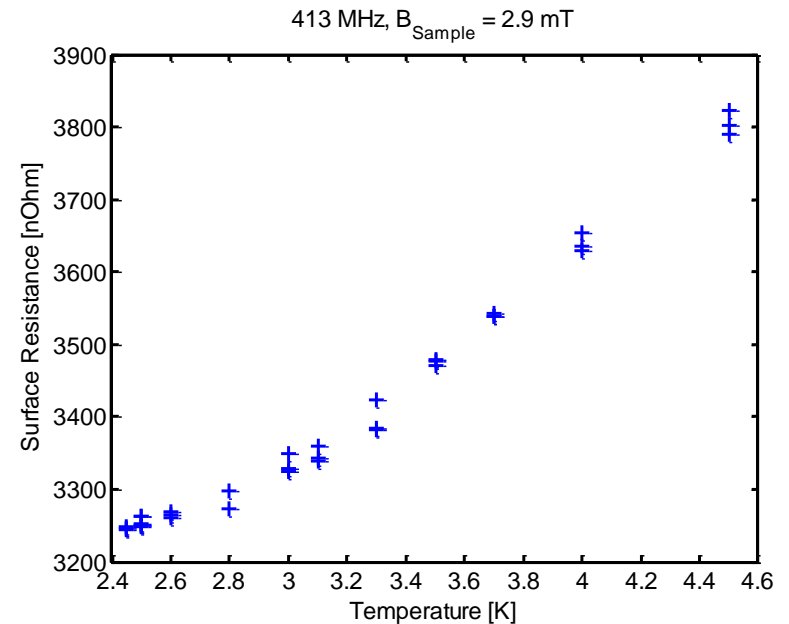
- First sample: with indium gasket
- (Too) high surface resistance
- Influence of indium at upper gasket visible
- Decrease of R_s at transition to nc Indium
- Second sample: no indium
- 850 °C bake before BCP
- Indium peak gone
- R_s still too high



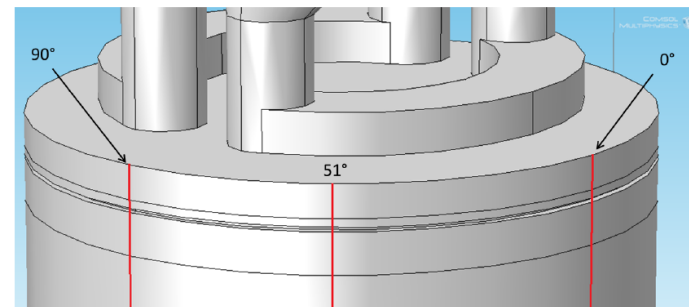
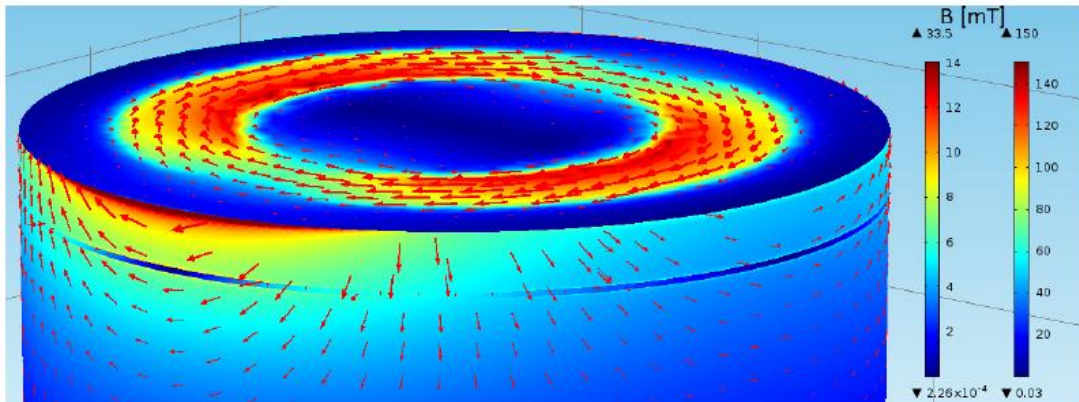
Indium (type I):

$$T_c = 3.4 \text{ K}$$

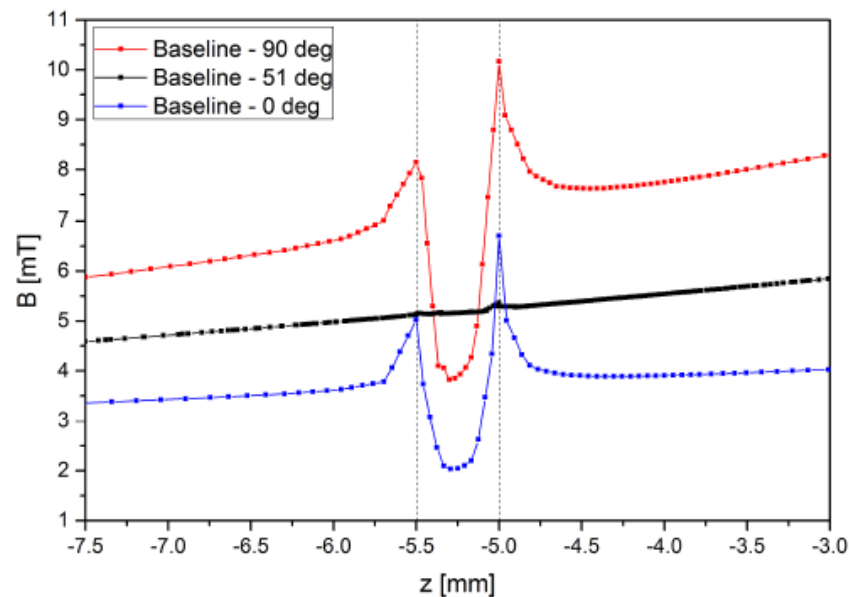
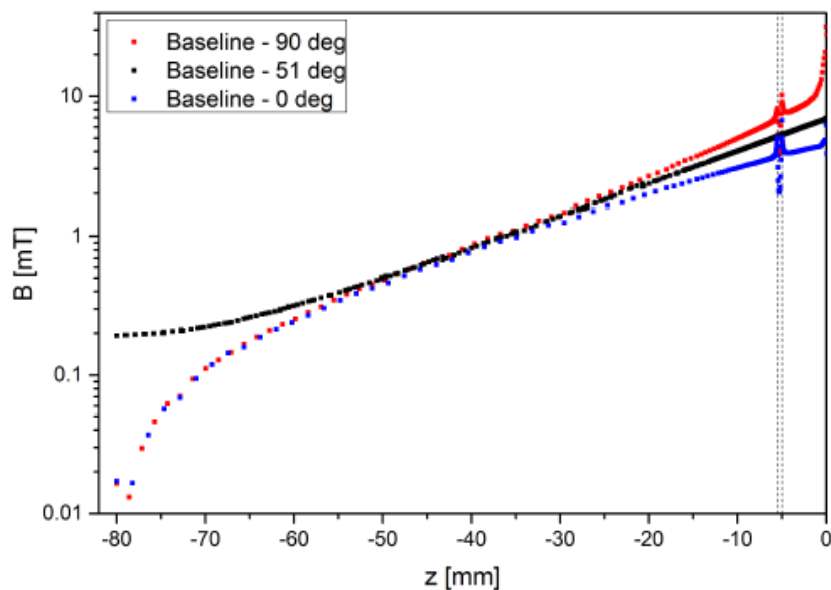
$$B_c = 28.5 \text{ mT}$$



- Multipacting
 - possible electron paths too short
- Paschen discharge
 - pressure times distance value too low
- Resistivity change at superconducting transition of Indium
 - does not explain increased surface resistance after sc transition
- Discontinuous thermal conductivity of Indium at T_c (Indium)
 - does not explain increased surface resistance after sc transition
- B-Field enhancement at interface sample/cylinder
 - maximum conceivable enhanced field too low
- Local quench
 - should exhibit different temperature dependence of R_s
- Q-disease
 - sample baked after BCP
- Mechanical stress in sample (new manufacturer REUTER from a Heraeus ingot)
 - should have been relaxed upon 850°C bake
- Anisotropy of RF currents in gap



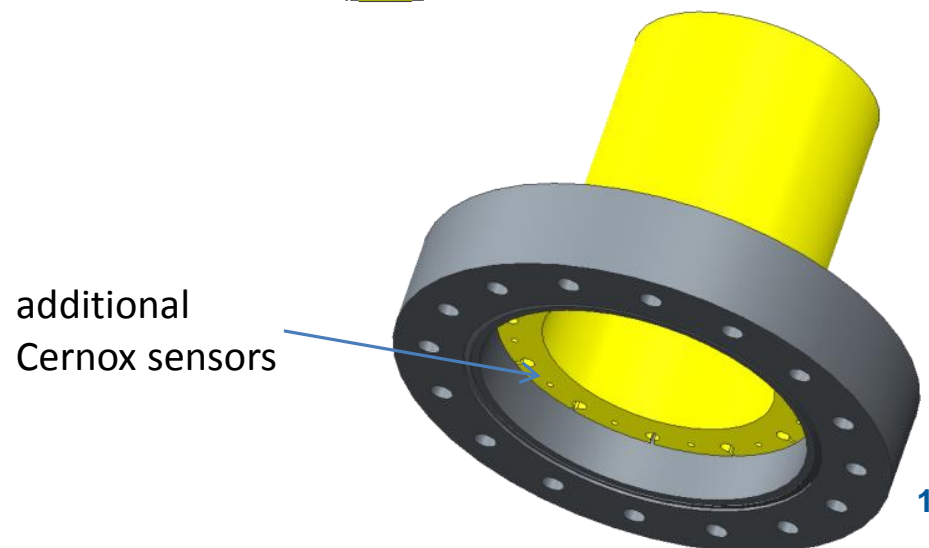
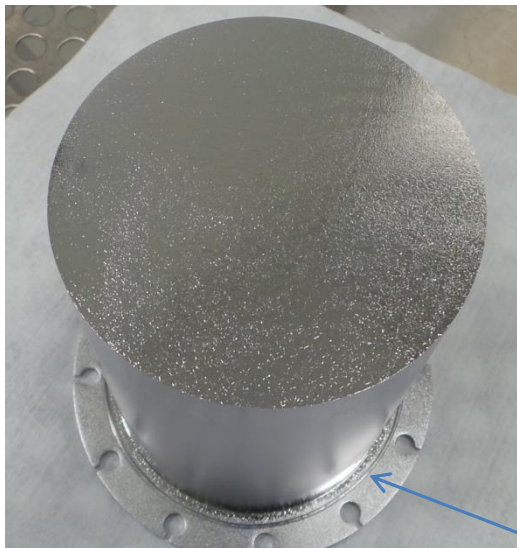
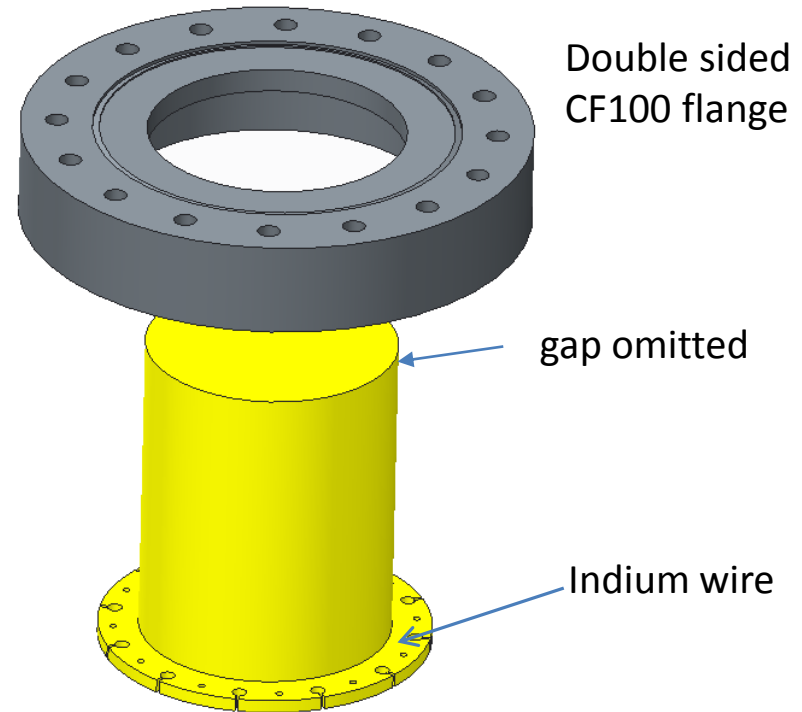
RF currents passing Indium in gap vertically



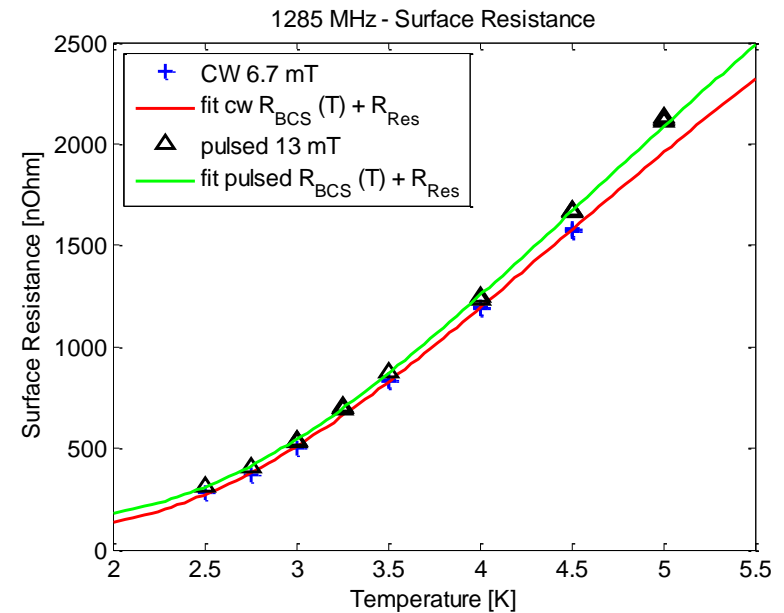
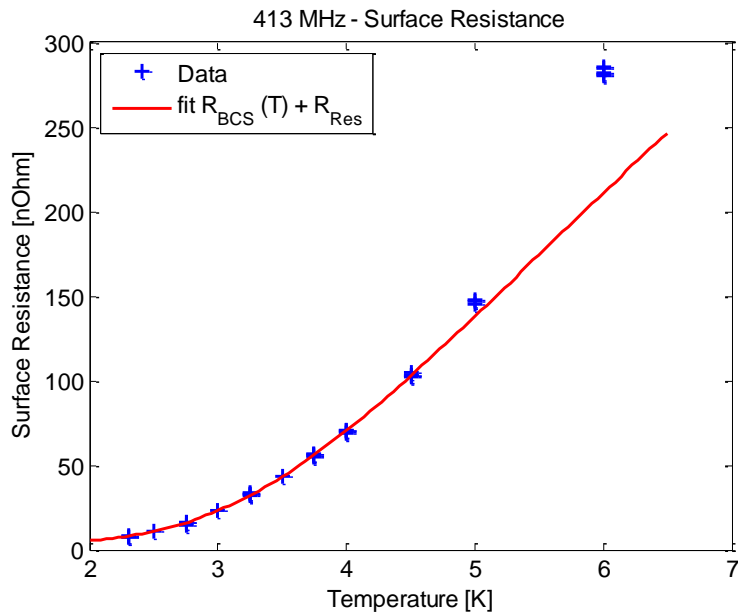
magnetic field in gap (150mT at sample)

Alternative calorimetry chamber II

- Pure Nb sample
→ high temperature treatments possible
 - Baking
 - N-doping
 - Diffusion coating (e.g. Nb₃Sn)
- UHV tight system
→ Indium wire gasket
- Height adjustment possible
- Short sample holder?
→ Electron beam welding required



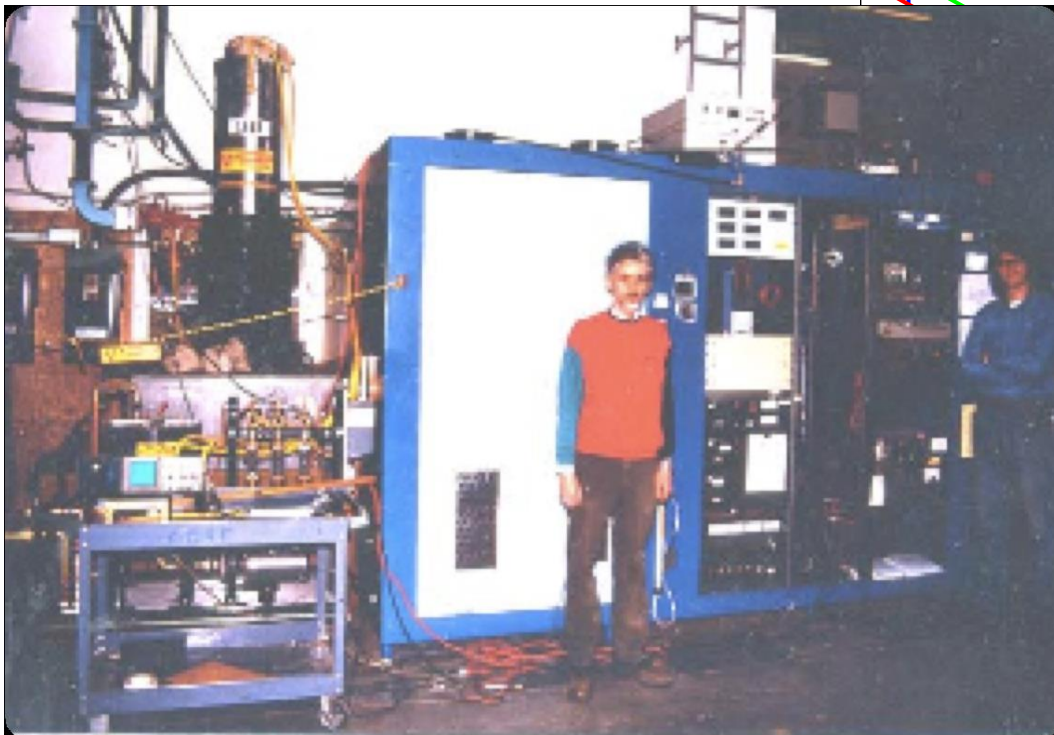
$$R_S = R_{BCS} + R_{res} = \frac{A\omega^2}{T} \exp\left(-\frac{\Delta}{k_B T}\right) + R_{res}$$



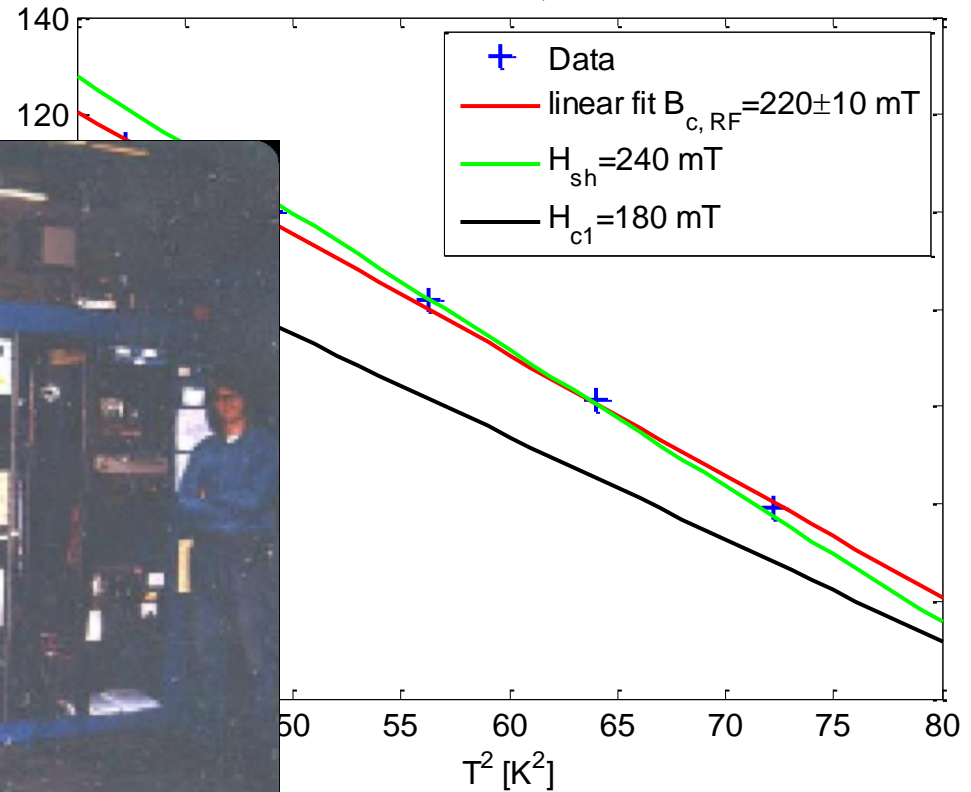
	413 MHz 16 mT, cw	1285 MHz 6.7 mT, cw	1285 MHz 13 mT, 30% DF
$A \left[\frac{\mu\Omega}{(\text{GHz})^2 \text{K}} \right]$	4.1 ± 0.2	2.86 ± 0.13	3.37 ± 0.15
Δ [meV]	1.60 ± 0.02	1.29 ± 0.02	1.34 ± 0.02
R_{res} [n Ω]	4.3 ± 0.5	83 ± 12	136 ± 12

- Pulsed RF power with small duty factor (DF)
- Increase power until quench occurs
- $B_c(T) = B_{c,0} \cdot \left(1 - \left(\frac{T}{T_c}\right)^2\right)$

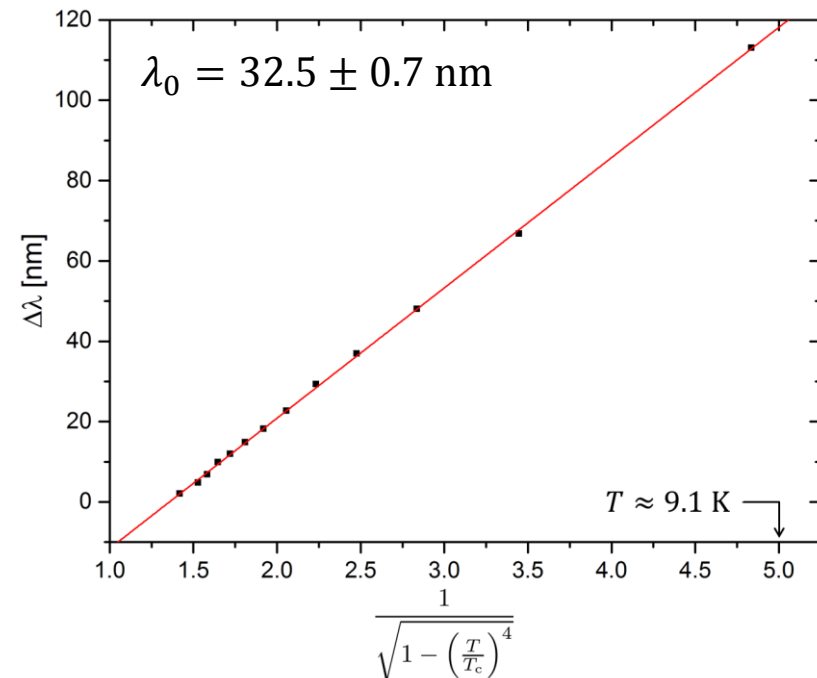
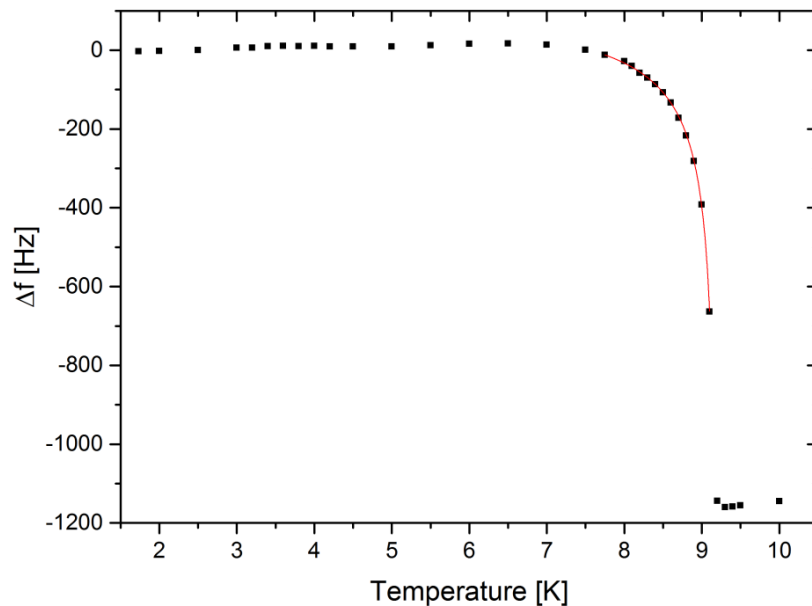
**Cavity: 1 MW klystron,
3 years of work**



RF critical field, 413 MHz



- Gorter-Casimir: $\lambda(T) = \frac{\lambda_0}{\sqrt{1 - \left(\frac{T}{T_c}\right)^4}}$
- Slater's Theorem and geometry factor of sample relate $\Delta\lambda = \lambda(T) - \lambda_0$ to Δf
- $\lambda(T = 0)$ from fit
→ electron mean free path l and RRR
- Value very close to $\lambda_L = 32$ nm

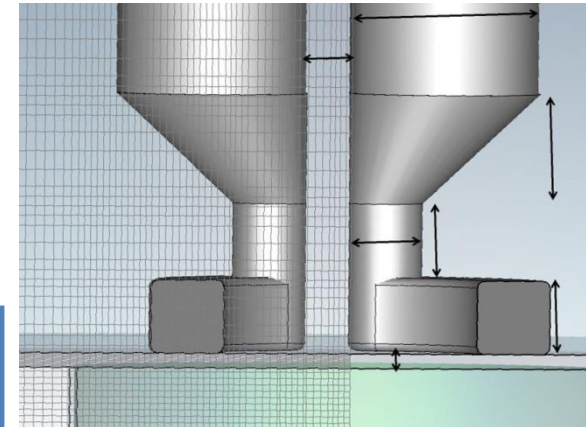


- QPR commissioned successfully
 - RF measurements up to 125 mT possible
 - Accuracy issues
- Simplified sample geometries investigated (ongoing)
 - Issues with Indium gasket
- Take part in followup projects:
 - ARIES (EuCARD3)
 - ANR-DFG proposal
 - EASITrain
- ToDo beyond Milestones and Deliverables:
Test first non-Nb sample
(if possible within last year of EuCARD2)



EuCARD-2 is co-funded by the partners and the European Commission under Capacities 7th Framework Programme, Grant Agreement 312453

- Optimization criteria
 - Phase space: Frequency, field strength, temperature
 - High resolution
- Full parameterization with CST
 - Maximizing figures of merit



	Baseline (CERN QPR)	Optimized
Operating frequencies	400 / 800 / 1200 MHz	433 / 866 / 1300 MHz (TESLA)
Focussing factor* $\frac{1}{U} \iint_{sample} H^2 dA$	$5.15 * 10^7 A^2/J$	$11.2 * 10^7 A^2/J$
Risk of field emission B_{Sample}/E_{pk}	4.68 mT/(MV/m)	7.44 mT/(MV/m)
Operating range B_{Sample}/B_{pk}	0.81	0.89
Microphonics 1st mechanical mode	69 Hz	172 Hz

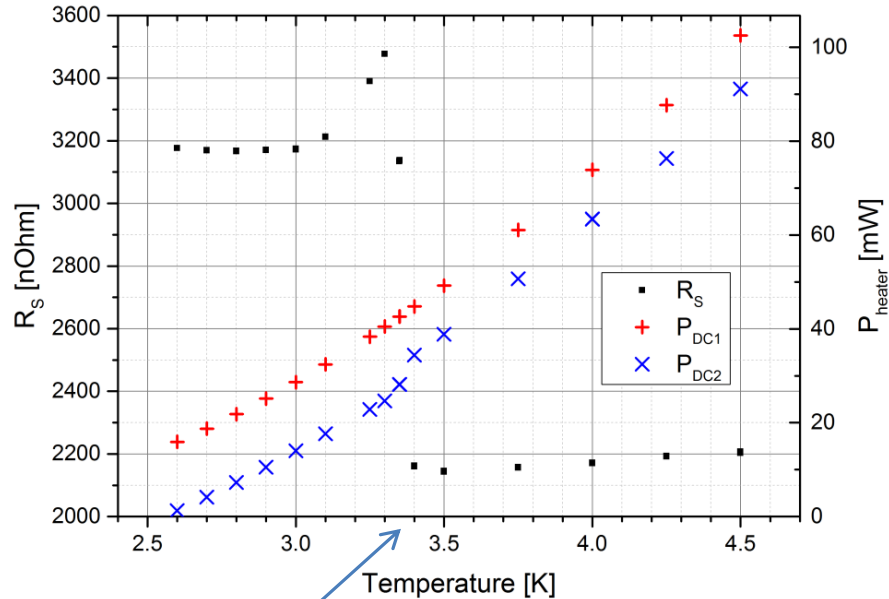
- Radius of rods increased
8 mm → 13 mm
- Gap reduced
(pole shoes ↔ sample)
1 mm → 0.5 mm

[R. Kleindienst, „Development of an Optimized Quadrupole Resonator at HZB“, SRF 2013]

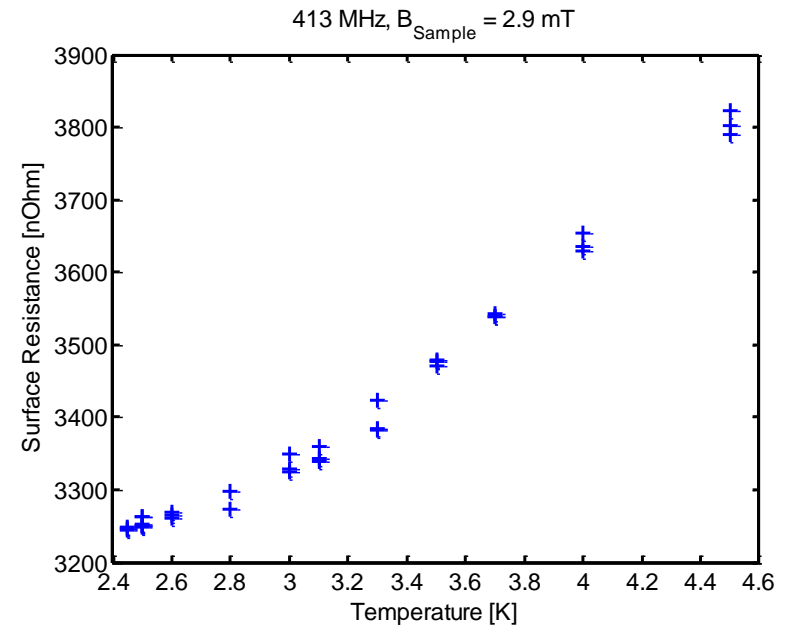
* fraction of field exposure between sample and resonator

- First sample: with indium gasket
- High surface resistance
- Influence of indium at upper gasket visible

- Second sample: no indium
- 850 °C bake before BCP



Indium: $T_c = 3.4$ K



- $$\frac{\Delta f}{f} = \frac{\frac{1}{4} \int_V^{V+\Delta V} (\epsilon_0 |E|^2 - \mu_0 |H|^2) dV}{U}$$
- Electric contribution negligible, $dV = dA d\lambda$
- $$\Delta\lambda = \lambda(T) - \lambda_0 = -\frac{G_{\text{Sample}}}{\pi\mu_0 f^2} \Delta f$$
- $$\lambda_0(l) = \lambda_L \sqrt{1 + \frac{\pi\xi_0}{2l}} \text{ (Pippard)}$$
- $$RRR \approx \frac{l [\text{nm}]}{2.7}$$

